



40V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C (Note 6)
-40V	$25m\Omega @ V_{GS} = -10V$	- 7.2A
	45mΩ @ V _{GS} = -4.5 V	- 5.4A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Printer Equipment

Features

- Low R_{DS(ON)} Minimizes Conduction Losses
- Fast Switching Speed Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMP4025SFGQ</u>)

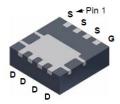
Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame.
 Solderable per MIL-STD-202, Method 208 ⁽²⁾
- Weight: 0.0172 grams (Approximate)

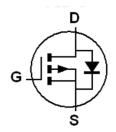




Top View



Bottom View



Device Symbol

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMP4025SFG-7	P40	7	8	2,000
DMP4025SFG-13	P40	13	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



P40 = Product Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	-40	\/
Gate-Source Voltage		V _{GSS}	±20	v I
Continuous Drain Current, V _{GS} = -10V	(Note 6)		-7.2	
	$T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	-5.77	
	(Note 5)		-4.65	
Maximum Body Diode Forward Current	(Note 6)	Is	-7.2	A
Pulsed Drain Current	(Note 7)	I _{DM}	-80	
Pulsed Source Current	(Note 7)	I _{SM}	-80	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

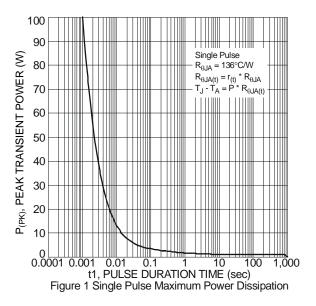
Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	Б	0.81	W	
Linear Derating Factor	(Note 6)	PD	1.95		
Thermal Resistance, Junction to Ambient	(Note 5)		155	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	64		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

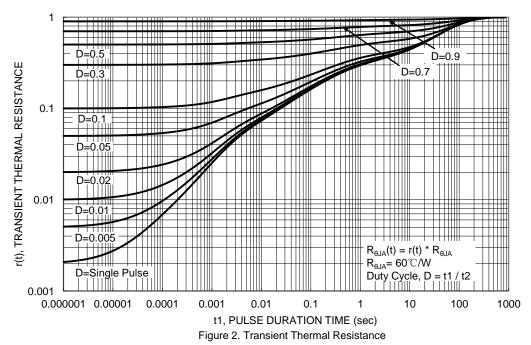
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with 2oz copper, in still air conditions.
 7. Same as note (6), except the device is pulsed with D= 0.02 and pulse width 300µs.



Thermal Characteristics







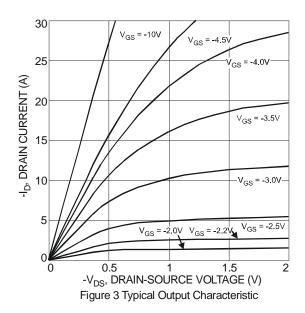
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

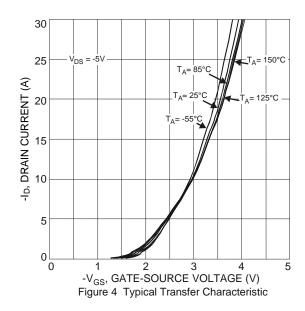
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	$I_D = -250\mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-0.8	-1.3	-1.8	V	$I_D = -250\mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	0		18	25	mΩ	$V_{GS} = -10V, I_D = -3A$	
Static Dialif-Source Off-Resistance (Note 6)	R _{DS(ON)}	ON) —	30	45		$V_{GS} = -4.5V, I_{D} = -3A$	
Forward Transconductance (Notes 8 & 9)	g _{fs}		16.6	_	S	$V_{DS} = -5V, I_{D} = -3A$	
Diode Forward Voltage (Note 8)	V_{SD}		-0.7	-1.0	V	$I_S = -1A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}		1643	_			
Output Capacitance	Coss		179	_	pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	128	_		I = IIVII IZ	
Gate Resistance	R_g	_	6.43	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (Note 10)	Qg	_	14.0	_		V _{GS} = -4.5V	
Total Gate Charge (Note 10)	Qg	_	33.7			V _{DS} = -20V	
Gate-Source Charge (Note 10)	Qgs	_	5.5	_	nC	$V_{GS} = -10V$ $I_D = -3A$	
Gate-Drain Charge (Note 10)	Q _{gd}	_	7.3				
Turn-On Delay Time (Note 10)	t _{D(ON)}		6.9	_			
Turn-On Rise Time (Note 10)	t _R		14.7	_]	$V_{DD} = -20V, V_{GS} = -10V$	
Turn-Off Delay Time (Note 10)	t _{D(OFF)}		53.7	_	ns	$I_D = -3A$	
Turn-Off Fall Time (Note 10)	t _F		30.9	_			

Notes:

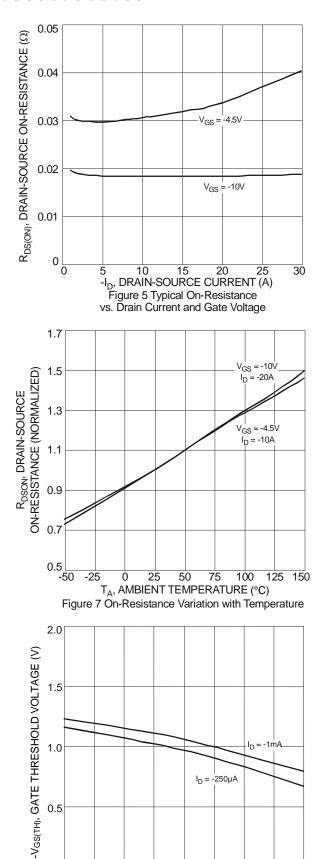
- 8. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.
- Weastled under pursed conditions. Furse width 2 500ps, duty cycle 2 2%.
 For design aid only, not subject to production testing.
 Switching characteristics are independent of operating junction temperatures.

Typical Characteristics









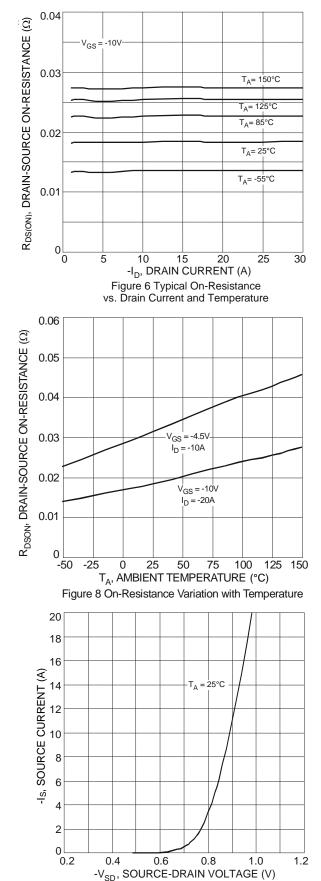


Figure 10 Diode Forward Voltage vs. Current

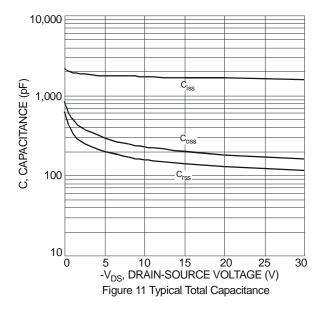
-50

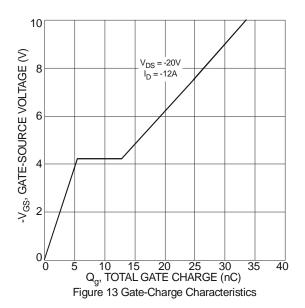
T_A, AMBIENT TEMPERATURE (°C)

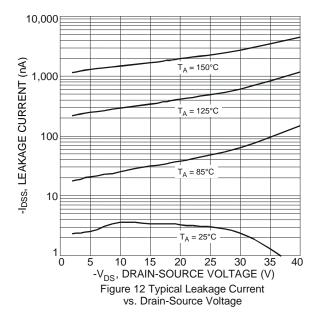
Figure 9 Gate Threshold Variation vs. Ambient Temperature

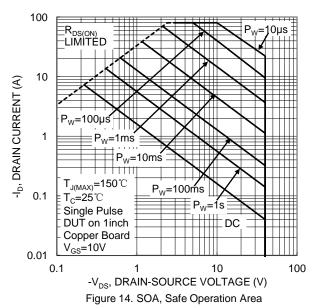
125 150









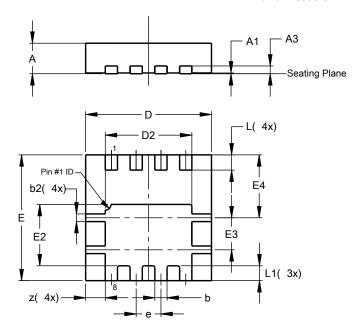




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

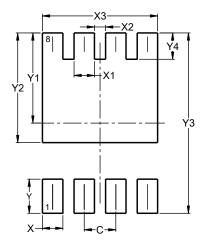


PowerDI3333-8				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.203	
b	0.27	0.37	0.32	
b2	0.15	0.25	0.20	
D	3.25	3.35	3.30	
D2	2.22	2.32	2.27	
E	3.25	3.35	3.30	
E2	1.56	1.66	1.61	
E3	0.79	0.89	0.84	
E4	1.60	1.70	1.65	
е	_	_	0.65	
L	0.35	0.45	0.40	
L1	_	_	0.39	
Z	_	_	0.515	
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
٧4	0.540



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